HFQ Series RF High Q Multilayer Chip Ceramic Capacitor

1. Capacitor characteristics and applications

1.1 Characteristics

- Size specifications are standardized and suitable for surface mount components in hybrid integrated circuits or printed circuits
- High Q value, low ESR, high reliability
- Low loss, high capacitance stability, high operating frequency
- Suitable for high-frequency circuits, VHF-microwave bands, RF and amplification circuits in various equipment

1.2 Main performance indicators

- Temperature coefficient: C0G: 0±30ppm/℃
- Capacitance drift: no more than±0.2% or ±0.05pF,whichever is larger.
- Quality factor (Q value): greater than 2,000 at a frequency of 1mHz/1kHz
- Insulation resistance: ≥100000mΩ at 20℃
- Operating temperature: -55～125℃

2. Product model naming

How to order

HFQ | 1111 | C0G | 1R0 | B | 501 | N | T

Type	Size	Dielectric	Capacitance unit: (pF)	Tolerance	Rated voltage	Termination	Packaging style
HFQ series RF high Q capacitor	0402 2525 0603 3838 0805 6243 0505 7676 1111	C0G: +30ppm/°C	The first two digits are significant figures, and the last digit is the power of 10	A: ±0.05pF B: ±0.10pF C: ±0.25pF D: ±0.50pF F: ±1.0% G: ±2.0% J: ±5.0% K: ±10.0%	The first two digits are significant figures, and the last digit is the power of 10	N: Leading-out Terminal: Ag/Ni/Sn Terminal: Z: Leading-out Ag/Ni/SnPb E: Non-magnetic Terminal M: Microstrip, A: Axial tape RW: Radial wire, RN: Non-magneticradialwire	T: Tape & reel C: Cut Tray B: Bulk